
2SD1367

Silicon NPN Epitaxial

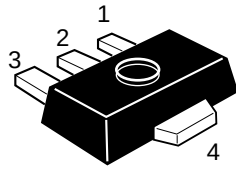
HITACHI

Application

- Low frequency power amplifier
- Complementary pair with 2SB1001

Outline

UPAK



1. Base
2. Collector
3. Emitter
4. Collector (Flange)

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	20	V
Collector to emitter voltage	V_{CEO}	16	V
Emitter to base voltage	V_{EBO}	6	V
Collector current	I_C	2	A
Collector peak current	$i_{C(peak)}^{*1}$	3	A
Collector power dissipation	P_C^{*2}	1	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	−55 to +150	°C

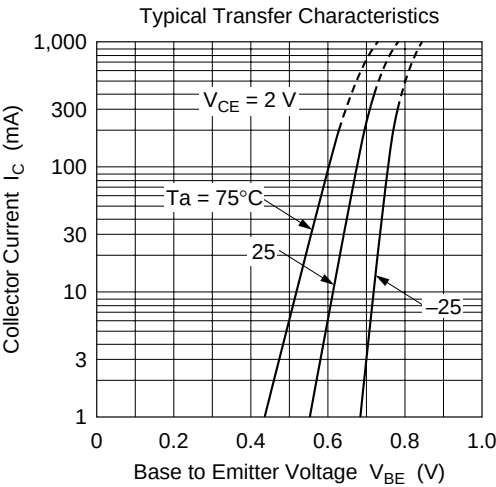
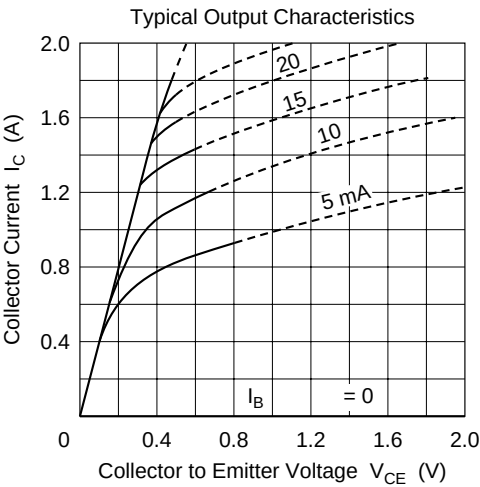
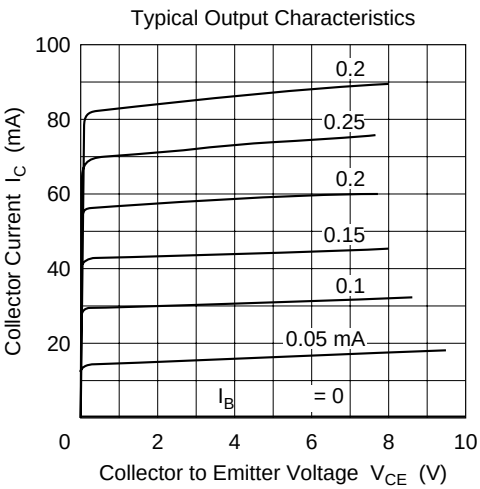
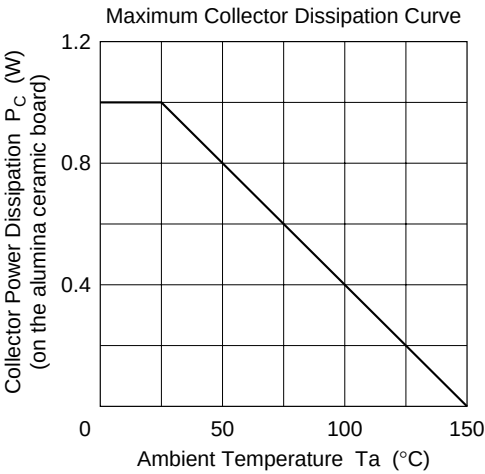
Notes: 1. $PW \leq 10$ ms, Duty cycle $\leq 20\%$.
2. Value on the alumina ceramic board (12.5 × 20 × 0.7 mm)

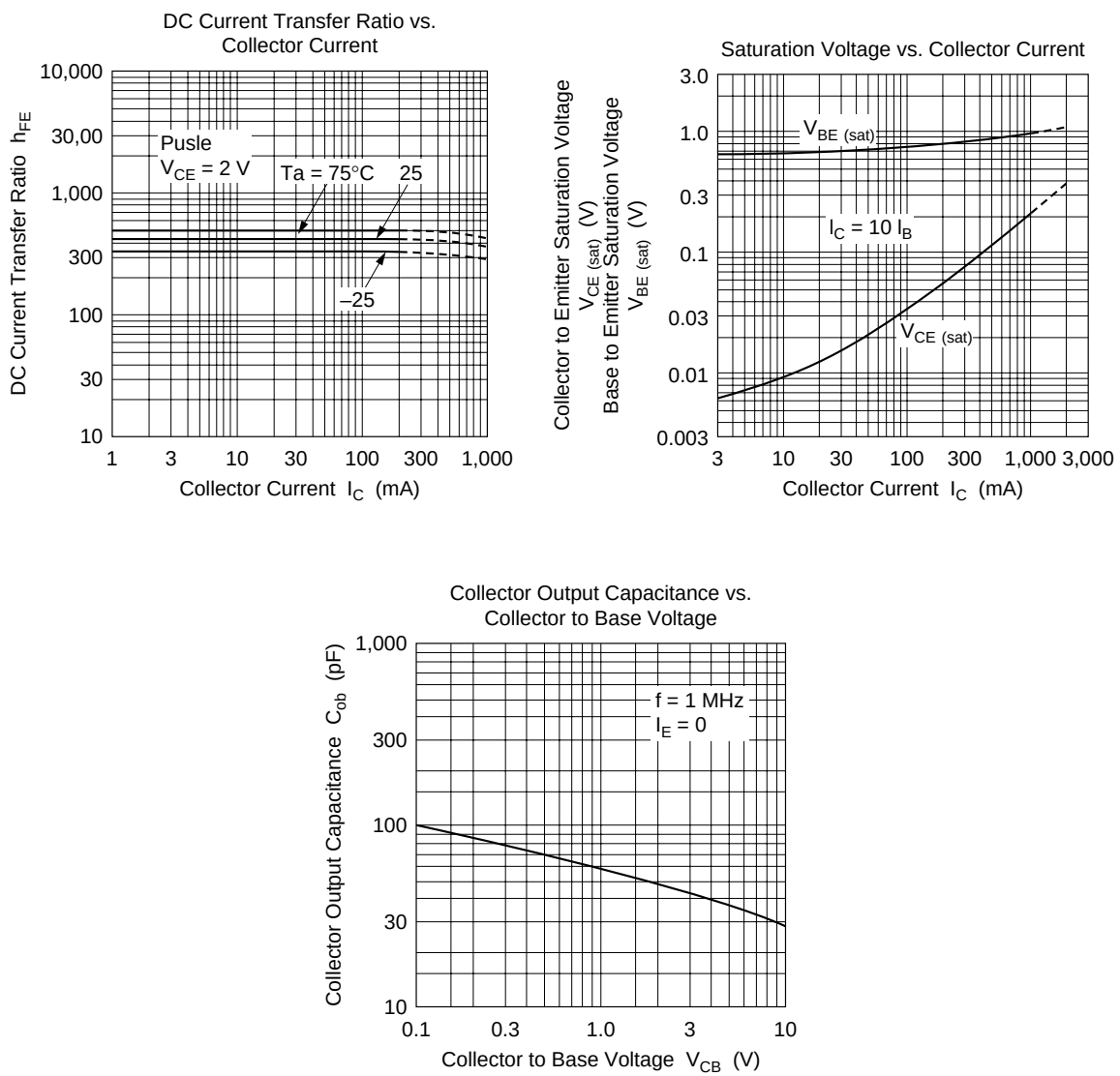
Electrical Characteristics (Ta = 25°C)

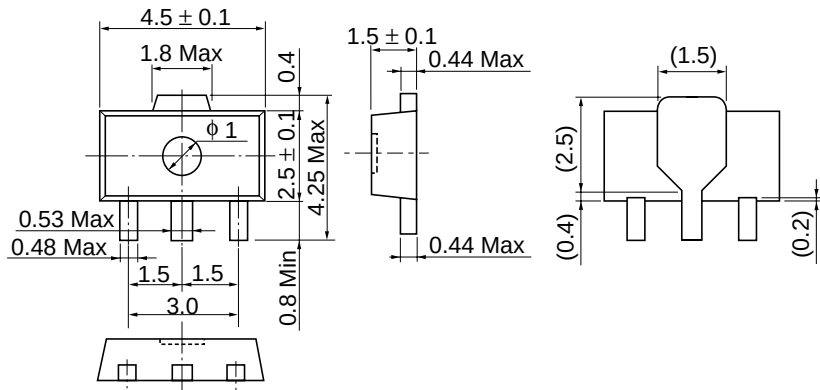
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	20	—	—	V	$I_C = 10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	16	—	—	V	$I_C = 1$ mA, $R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	6	—	—	V	$I_E = 10 \mu A, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	0.1	μA	$V_{CB} = 16$ V, $I_E = 0$
Emitter cutoff current	I_{EBO}	—	—	0.1	μA	$V_{EB} = 5$ V, $I_C = 0$
DC current transfer ratio	h_{FE}^{*1}	100	—	500		$V_{CE} = 2$ V, $I_C = 0.1$ A, Pulse
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	0.15	0.3	V	$I_C = 1$ A, $I_B = 0.1$ A, Pulse
Base to emitter saturation voltage	$V_{BE(sat)}$	—	0.9	1.2	V	$I_C = 1$ A, $I_B = 0.1$ A, Pulse
Gain bandwidth product	f_T	—	100	—	MHz	$V_{CE} = 2$ V, $I_C = 10$ mA
Collector output capacitance	C_{ob}	—	20	—	pF	$V_{CB} = 10$ V, $I_E = 0, f = 1$ MHz

Note: 1. The 2SD1367 is grouped by h_{FE} as follows.

Mark	BA	BB	BC
h_{FE}	100 to 200	160 to 320	250 to 500







Hitachi Code	UPAK
JEDEC	—
EIAJ	Conforms
Weight (reference value)	0.050 g

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